

Sheet 1 of 1

FORM PTO 1449 (modified)
 U.S. DEPARTMENT OF COMMERCE
 PATENT AND TRADEMARK OFFICE
 LIST OF REFERENCES CITED BY APPLICANT(S)
 (Use several sheets if necessary)
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APPLICANTS
 Sindo Kou, et al.

FILING DATE

GROUP

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MS	4,594,173	6/10/86	Hobgood, et al.			
MS	4,645,560	2/24/87	Matsumoto, et al.			
MS	4,654,110	3/31/87	Morrison			
MS	4,668,481	5/26/87	Watanabe, et al.			
MS	4,686,091	8/11/87	Washizuka, et al.			
MS	4,734,267	3/29/88	Kojima			
MS	5,021,118	6/4/91	Kawasaki			
MS	5,515,810	5/14/96	Yamashita			
MS	5,851,850	12/22/98	Yanagisawa, et al.			
MS	6,143,070	11/7/00	Bliss, et al.			

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

MS		William G. Pfann, Zone Melting (Book), John Wiley & Sons, Inc., 1966, pp. 199-214.
MS		I.R.W. Ware, "LEC Growth of Bulk InxGal-xAs," Report ADA 297039, Defense Technical Information Center, Ft. Belvoir, VA, 1995.
MS		Handbook of Crystal Growth 2 (Book), D.T.J. Hurle, Ed., North-Holland, Elsevier Science B.V., 1994, Chapter 2 (Bridgman and Related Growth Techniques), pp. 53-58.
MS		M.H. Lin, et al., "Dopant Segregation in Crystal Pulling with Bottom Melt Replenishing," J. of Crystal Growth, Vol. 142, 1994, pp. 392-396.
MS		Kazuo Nakajima, et al., "Constant Temperature LEC Growth of InGaAs Ternary Bulk Crystals Using the Double Crucible Method," J. of Crystal Growth, Vol. 169, 1996, pp. 217-222.

100			M.H. Lin, et al., "Czochralski Pulling of InSb Single Crystals from a Molten Zone on a Solid Feed," J. of Crystal Growth, Vol. 193, 1998, pp. 443-445.
105			J. He, et al., "A New Double Crucible Technique for LEC Growth of In-Doped GaAs Crystals," J. of Crystal Growth, Vol. 208, 2000, pp. 42-48.
110			J. He, et al., "Double Crucible LEC Growth of In-Doped GaAs Using Inner Crucibles with a Bottom Tube," J. of Crystal Growth, Vol. 211, 2000, pp. 163-168.
EXAMINER	M.H. Lin, et al.		DATE CONSIDERED 7/3/2

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant..